

FIN FIELD EFFECT TRANSISTOR WITH SELF-ALIGNED GATE

ABSTRACT OF THE DISCLSOURE

The present invention provides a process for fabricating a metal oxide semiconductor
5 field effect transistor (MOSFET) having a double-gate and a double-channel wherein
the gate region is self-aligned to the channel regions and the source/drain diffusion
junctions. The present invention also relates to the FIN MOSFFET structure which is
formed using method of the present invention.